## 74HC1G32-Q100; 74HCT1G32-Q100

## 2-input OR gate

Rev. 1 — 8 August 2012

**Product data sheet** 

### 1. General description

74HC1G32-Q100 and 74HCT1G32-Q100 are high-speed Si-gate CMOS devices. They provide a 2-input OR function.

The standard output currents are half of those of the 74HC32-Q100 and 74HCT32-Q100.

This product has been qualified to the Automotive Electronics Council (AEC) standard Q100 (Grade 1) and is suitable for use in automotive applications.

#### 2. Features and benefits

- Automotive product qualification in accordance with AEC-Q100 (Grade 1)
  - ◆ Specified from -40 °C to +85 °C and from -40 °C to +125 °C
- Input levels:
  - ◆ For 74HC1G32-Q100: CMOS level
  - ◆ For 74HCT1G32-Q100: TTL level
- Symmetrical output impedance
- High noise immunity
- Low power dissipation
- Balanced propagation delays
- ESD protection:
  - ◆ MIL-STD-883, method 3015 exceeds 2000 V
  - ◆ HBM JESD22-A114F exceeds 2000 V
  - ♦ MM JESD22-A115-A exceeds 200 V (C = 200 pF, R = 0 Ω)
- SOT353-1 and SOT753 package options

### 3. Ordering information

Table 1. Ordering information

Type number	Package	Package					
	Temperature range	Name	Description	Version			
74HC1G32GW-Q100	–40 °C to +125 °C	TSSOP5					
74HCT1G32GW-Q100			body width 1.25 mm				
74HC1G32GV-Q100	–40 °C to +125 °C	SC-74A	plastic surface-mounted package; 5 leads	SOT753			
74HCT1G32GV-Q100							



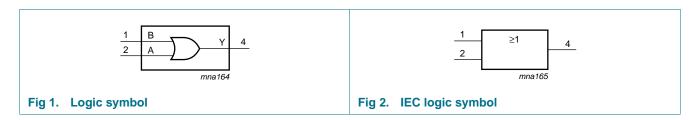
### 4. Marking

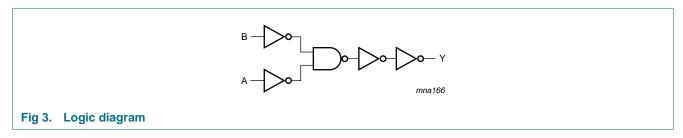
#### Table 2. Marking codes

Type number	Marking code <sup>[1]</sup>
74HC1G32GW-Q100	HG
74HCT1G32GW-Q100	TG
74HC1G32GV-Q100	H32
74HCT1G32GV-Q100	T32

<sup>[1]</sup> The pin 1 indicator is located on the lower left corner of the device, below the marking code.

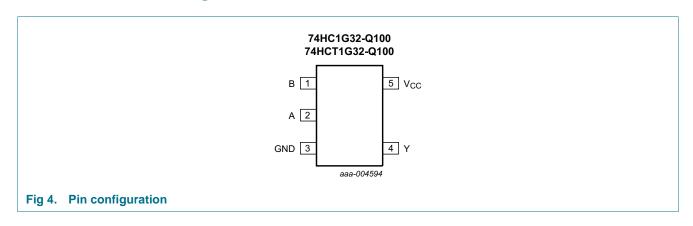
### 5. Functional diagram





## 6. Pinning information

#### 6.1 Pinning



### 6.2 Pin description

Table 3. Pin description

Symbol	Pin	Description
В	1	data input B
A	2	data input A
GND	3	ground (0 V)
Υ	4	data output Y
V <sub>CC</sub>	5	supply voltage

### 7. Functional description

#### Table 4. Function table

H = HIGH voltage level; L = LOW voltage level

Inputs		Output
Α	В	Υ
L	L	L
L	Н	Н
Н	L	Н
Н	Н	Н

### 8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V). [1]

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{CC}$	supply voltage		-0.5	+7.0	V
I <sub>IK</sub>	input clamping current	$V_I < -0.5 \text{ V or } V_I > V_{CC} + 0.5 \text{ V}$	-	±20	mA
I <sub>OK</sub>	output clamping current	$V_O$ < $-0.5$ V or $V_O$ > $V_{CC}$ + $0.5$ V	-	±20	mA
Io	output current	$-0.5 \text{ V} < \text{V}_{\text{O}} < \text{V}_{\text{CC}} + 0.5 \text{ V}$	-	±12.5	mA
I <sub>CC</sub>	supply current		-	25	mA
$I_{GND}$	ground current		-25	-	mA
T <sub>stg</sub>	storage temperature		-65	+150	°C
P <sub>tot</sub>	total power dissipation	$T_{amb} = -40  ^{\circ}\text{C} \text{ to } +125  ^{\circ}\text{C}$	[2] _	200	mW

<sup>[1]</sup> The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

<sup>[2]</sup> Above 55  $^{\circ}$ C the value of P<sub>tot</sub> derates linearly with 2.5 mW/K.

## 9. Recommended operating conditions

Table 6. Recommended operating conditions

Voltages are referenced to GND (ground = 0 V).

Symbol	I Parameter Conditions		74HC1G32-Q100			74HCT1G32-Q100			Unit
			Min	Тур	Max	Min	Тур	Max	
$V_{CC}$	supply voltage		2.0	5.0	6.0	4.5	5.0	5.5	V
VI	input voltage		0	-	$V_{CC}$	0	-	$V_{CC}$	V
Vo	output voltage		0	-	$V_{CC}$	0	-	$V_{CC}$	V
T <sub>amb</sub>	ambient temperature		-40	+25	+125	-40	+25	+125	°C
$\Delta t / \Delta V$	input transition rise	$V_{CC} = 2.0 \text{ V}$	-	-	625	-	-	-	ns/V
and fall rate	and fall rate	V <sub>CC</sub> = 4.5 V	-	-	139	-	-	139	ns/V
		V <sub>CC</sub> = 6.0 V	-	-	83	-	-	-	ns/V

### 10. Static characteristics

Table 7. Static characteristics

Voltages are referenced to GND (ground = 0 V). All typical values are measured at T<sub>amb</sub> = 25 °C.

Symbol	Parameter	Conditions	-40	°C to +8	35 °C	–40 °C t	o +125 °C	Unit
				Тур	Max	Min	Max	
74HC1G3	2-Q100							
$V_{IH}$	HIGH-level input	V <sub>CC</sub> = 2.0 V	1.5	1.2	-	1.5	-	V
	voltage	V <sub>CC</sub> = 4.5 V	3.15	2.4	-	3.15	-	V
		V <sub>CC</sub> = 6.0 V	4.2	3.2	-	4.2	-	V
$V_{IL}$	LOW-level input	V <sub>CC</sub> = 2.0 V	-	0.8	0.5	-	0.5	V
voltage	V <sub>CC</sub> = 4.5 V	-	2.1	1.35	-	1.35	V	
		V <sub>CC</sub> = 6.0 V	-	2.8	1.8	-	1.8	V
$V_{OH}$	HIGH-level output	$V_I = V_{IH}$ or $V_{IL}$						
voltage	voltage	$I_O = -20 \mu A; V_{CC} = 2.0 V$	1.9	2.0	-	1.9	-	V
		$I_O = -20 \mu A; V_{CC} = 4.5 V$	4.4	4.5	-	4.4	-	V
		$I_O = -20 \mu A; V_{CC} = 6.0 V$	5.9	6.0	-	5.9	-	V
		$I_O = -2.0$ mA; $V_{CC} = 4.5$ V	4.13	4.32	-	3.7	-	V
		$I_{O} = -2.6 \text{ mA}; V_{CC} = 6.0 \text{ V}$	5.63	5.81	-	5.2	-	V
$V_{OL}$	LOW-level output	$V_I = V_{IH}$ or $V_{IL}$						
	voltage	$I_O = 20 \mu A; V_{CC} = 2.0 V$	-	0	0.1	-	0.1	V
		$I_O = 20 \mu A; V_{CC} = 4.5 V$	-	0	0.1	-	0.1	V
		$I_O = 20 \mu A; V_{CC} = 6.0 V$	-	0	0.1	-	0.1	V
		$I_O = 2.0 \text{ mA}; V_{CC} = 4.5 \text{ V}$	-	0.15	0.33	-	0.4	V
		$I_O = 2.6 \text{ mA}; V_{CC} = 6.0 \text{ V}$	-	0.16	0.33	-	0.4	V
I <sub>I</sub>	input leakage current	$V_I = V_{CC}$ or GND; $V_{CC} = 6.0 \text{ V}$	-	-	1.0	-	1.0	μΑ
I <sub>CC</sub>	supply current	$V_I = V_{CC}$ or GND; $I_O = 0$ A; $V_{CC} = 6.0 \text{ V}$	-	-	10	-	20	μА
Cı	input capacitance		-	1.5	-	-	-	pF

 Table 7.
 Static characteristics ...continued

Voltages are referenced to GND (ground = 0 V). All typical values are measured at  $T_{amb}$  = 25 °C.

Symbol	Parameter	ter Conditions		°C to +8	85 °C	-40 °C t	Unit	
-			Min	Тур	Max	Min	Max	
74HCT1G	32-Q100					I		
$V_{IH}$	HIGH-level input voltage	$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$	2.0	1.6	-	2.0	-	V
$V_{IL}$	LOW-level input voltage	$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$	-	1.2	8.0	-	0.8	V
V <sub>OH</sub>	HIGH-level output	$V_I = V_{IH}$ or $V_{IL}$ ; $V_{CC} = 4.5 \text{ V}$						
	voltage	$I_{O} = -20 \mu A$	4.4	4.5	-	4.4	-	V
		$I_{O} = -2.0 \text{ mA}$	4.13	4.32	-	3.7	-	V
V <sub>OL</sub>	LOW-level output	$V_I = V_{IH}$ or $V_{IL}$ ; $V_{CC} = 4.5 \text{ V}$						
	voltage	I <sub>O</sub> = 20 μA	-	0	0.1	-	0.1	V
		$I_{O} = 2.0 \text{ mA}$	-	0.15	0.33	-	0.4	V
I <sub>I</sub>	input leakage current	$V_I = V_{CC}$ or GND; $V_{CC} = 5.5 \text{ V}$	-	-	1.0	-	1.0	μΑ
I <sub>CC</sub>	supply current	$V_I = V_{CC}$ or GND; $I_O = 0$ A; $V_{CC} = 5.5 \text{ V}$	-	-	10	-	20	μΑ
$\Delta I_{CC}$	additional supply current	per input; $V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$ ; $V_I = V_{CC} - 2.1 \text{ V}$ ; $I_O = 0 \text{ A}$	-	-	500	-	850	μΑ
Cı	input capacitance		-	1.5	-	-	-	pF

## 11. Dynamic characteristics

Table 8. Dynamic characteristics

GND = 0 V;  $t_r = t_f \le 6.0$  ns. All typical values are measured at  $T_{amb} = 25$  °C. For test circuit see <u>Figure 6</u>

Symbol	ymbol Parameter Conditions		–40 °C to +85 °		5 °C	–40 °C t	°C to +125 °C		
				Min	Тур	Max	Min	Max	
74HC1G	32-Q100						'	1	
t <sub>pd</sub>	propagation delay	A and B to Y; see Figure 5	<u>[1]</u>						
		$V_{CC} = 2.0 \text{ V}; C_L = 50 \text{ pF}$		-	18	115	-	135	ns
		$V_{CC} = 4.5 \text{ V}; C_L = 50 \text{ pF}$		-	8	23	-	27	ns
		$V_{CC} = 5.0 \text{ V}; C_L = 15 \text{ pF}$		-	8	-	-	-	ns
		$V_{CC} = 6.0 \text{ V}; C_L = 50 \text{ pF}$		-	7	20	-	23	ns
$C_{PD}$	power dissipation capacitance	$V_I = GND \text{ to } V_{CC}$	[2]	-	19	-	-	-	pF

 Table 8.
 Dynamic characteristics ...continued

GND = 0 V;  $t_r = t_f \le 6.0$  ns. All typical values are measured at  $T_{amb} = 25$  °C. For test circuit see Figure 6

	, , ,	, i	arrio						
Symbol Parameter Conditions			-40 °C to +85 °C			-40 °C t	Unit		
				Min	Тур	Max	Min	Max	
74HCT1	G32-Q100		'			'			
t <sub>pd</sub>	propagation delay	A and B to Y; see Figure 5	[1]						
		$V_{CC} = 4.5 \text{ V}; C_L = 50 \text{ pF}$		-	10	24	-	27	ns
		$V_{CC} = 5.0 \text{ V}; C_L = 15 \text{ pF}$		-	10	-	-	-	ns
$C_{PD}$	power dissipation capacitance	$V_I = GND \text{ to } V_{CC} - 1.5 \text{ V}$	[2]	-	20	-	-	-	pF

- [1]  $t_{pd}$  is the same as  $t_{PLH}$  and  $t_{PHL}$ .
- [2]  $C_{PD}$  is used to determine the dynamic power dissipation  $P_D$  ( $\mu W$ ).

 $P_D = C_{PD} \times V_{CC}{}^2 \times f_i + \sum \left( C_L \times V_{CC}{}^2 \times f_o \right)$  where:

 $f_i$  = input frequency in MHz

fo = output frequency in MHz

 $C_L$  = output load capacitance in pF

V<sub>CC</sub> = supply voltage in V

 $\sum (C_L \times V_{CC}^2 \times f_o) = \text{sum of outputs}$ 

#### 12. Waveforms

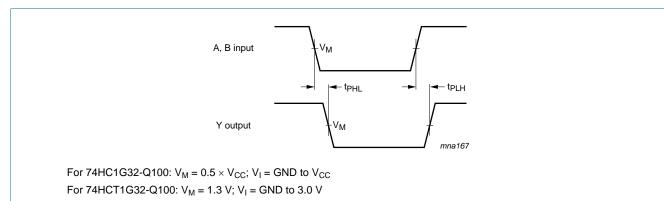
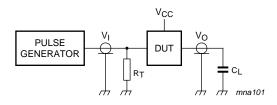


Fig 5. The input (A and B) to output (Y) propagation delays



Measurement points are given in Table 8. Definitions for test circuit:

C<sub>L</sub> = Load capacitance including jig and probe capacitance.

 $R_T$  = Termination resistance should be equal to output impedance  $Z_0$  of the pulse generator.

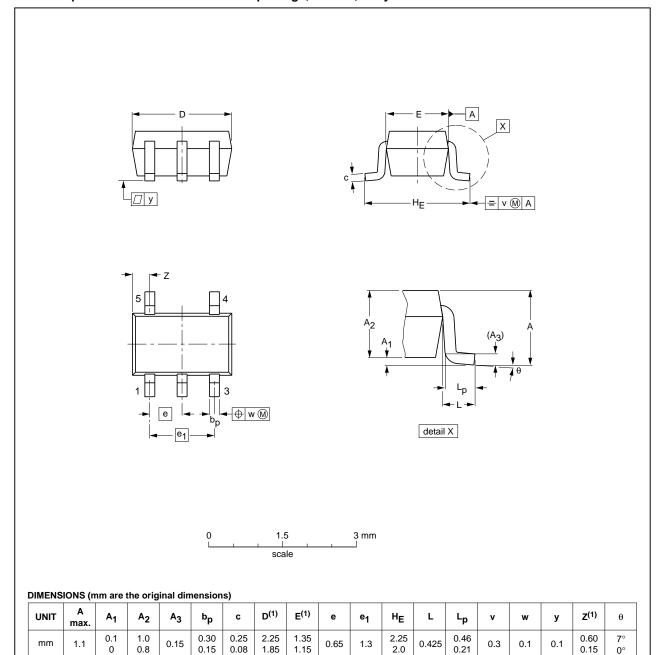
Fig 6. Load circuitry for switching times

74HC\_HCT1G32\_Q100

### 13. Package outline

TSSOP5: plastic thin shrink small outline package; 5 leads; body width 1.25 mm

SOT353-1



1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.

OUTLINE		REFER	ENCES	EUROPEAN	ISSUE DATE
VERSION	IEC	JEDEC	JEITA	PROJECTION ISSUE DA	
SOT353-1		MO-203	SC-88A		<del>-00-09-01-</del> 03-02-19

Fig 7. Package outline SOT353-1 (TSSOP5)

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#### Plastic surface-mounted package; 5 leads

**SOT753** 

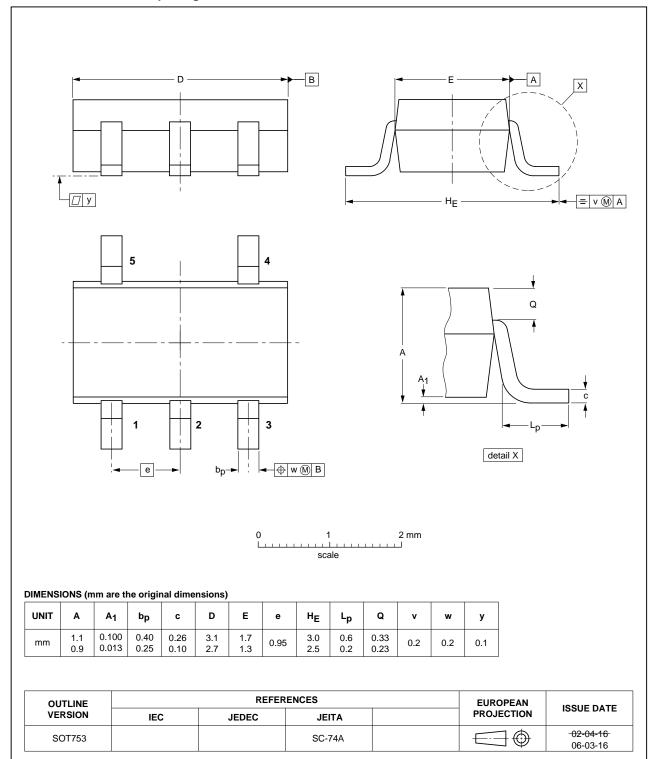


Fig 8. Package outline SOT753 (SC-74A)

8 of 12

### 14. Abbreviations

#### Table 9. Abbreviations

Acronym	Description
CMOS	Complementary Metal Oxide Semiconductor
TTL	Transistor-Transistor Logic
НВМ	Human Body Model
ESD	ElectroStatic Discharge
MM	Machine Model
DUT	Device Under Test
MIL	Military

## 15. Revision history

#### Table 10. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74HC_HCT1G32_Q100 v.1	20120808	Product data sheet	-	-

### 16. Legal information

#### 16.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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74HC\_HCT1G32\_Q100

## 74HC1G32-Q100; 74HCT1G32-Q100

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2-input OR gate

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#### 18. Contents

1	General description
2	Features and benefits
3	Ordering information 1
4	Marking 2
5	Functional diagram 2
6	Pinning information 2
6.1	Pinning
6.2	Pin description
7	Functional description 3
8	Limiting values 3
9	Recommended operating conditions 4
10	Static characteristics 4
11	Dynamic characteristics 5
12	Waveforms 6
13	Package outline
14	Abbreviations 9
15	Revision history 9
16	Legal information
16.1	Data sheet status
16.2	Definitions
16.3	Disclaimers
16.4	Trademarks11
17	Contact information 11
12	Contents 12

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